

NTMS4503N

Power MOSFET

28 V, 14 A, N-Channel, SOIC-8

Features

- Low $R_{DS(on)}$
- High Power and Current Handling Capability
- Low Gate Charge
- Pb-Free Package is Available

Applications

- DC/DC Converters
- Motor Drives
- Synchronous Rectifier – POL
- Buck Low-Side

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|-----------|--|------------------|
| Drain-to-Source Voltage | V_{DSS} | 28 | V |
| Gate-to-Source Voltage – Continuous | V_{GS} | ± 20 | V |
| Drain Current | I_D | Continuous @ $T_A = 25^\circ\text{C}$ (Note 1) | 14 |
| | | Continuous @ $T_A = 25^\circ\text{C}$ (Note 2) | 12 |
| | | Continuous @ $T_A = 25^\circ\text{C}$ (Note 3) | 9.0 |
| | | Single Pulse ($t_p = 10 \mu\text{s}$) | 40 |
| Total Power Dissipation | P_D | $T_A = 25^\circ\text{C}$ (Note 1) | 2.5 |
| | | $T_A = 25^\circ\text{C}$ (Note 2) | 1.66 |
| | | $T_A = 25^\circ\text{C}$ (Note 3) | 0.93 |
| | | Operating and Storage Temperature | T_J, T_{stg} |
| Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_L = 12.2 \text{ A}$, $L = 1.0 \text{ mH}$, $R_G = 25 \Omega$) | E_{AS} | 75 | mJ |
| Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds | T_L | 260 | $^\circ\text{C}$ |

THERMAL RESISTANCE RATINGS

| Rating | Symbol | Value | Unit |
|--------------------|-----------------|------------------------------|------|
| Thermal Resistance | $R_{\theta JA}$ | Junction-to-Ambient (Note 1) | 50 |
| | | Junction-to-Ambient (Note 2) | 75 |
| | | Junction-to-Ambient (Note 3) | 135 |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

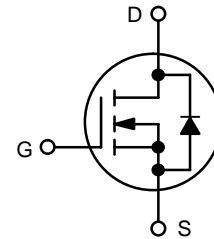
1. Surface-mounted on FR4 board using minimum recommended pad size (Cu area 0.412 in sq), $t < 10 \text{ s}$.
2. Surface-mounted on FR4 board using 1" pad size (Cu area 1.127 in sq) steady state.
3. Surface-mounted on FR4 board using minimum recommended pad size (Cu area 0.412 in sq), steady state.



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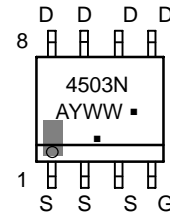
| $V_{(BR)DSS}$ | $R_{DS(on)}$ TYP | I_D Max (Note 1) |
|---------------|------------------------|--------------------|
| 28 V | 7.0 m Ω @ 10 V | 14 A |
| | 8.8 m Ω @ 4.5 V | |



MARKING DIAGRAM & PIN ASSIGNMENT



SOIC-8
CASE 751
STYLE 12



4503N = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping† |
|--------------|---------------------|------------------|
| NTMS4503NR2 | SOIC-8 | 2500/Tape & Reel |
| NTMS4503NR2G | SOIC-8 (Pb-Free) | 2500/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTMS4503N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|----------------|--------|----------------|-----|-----|-----|------|
|----------------|--------|----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|---|--------------------------------------|--|------------------------|----|------|-------|
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} = 0 V, I _D = 250 μA | 28 | 31 | – | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V _{(BR)DSS} /T _J | – | – | 22 | – | mV/°C |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V, V _{DS} = 24 V | T _J = 25°C | | 1.0 | μA |
| | | | T _J = 100°C | | 25 | |
| Gate-to-Source Leakage Current | I _{GSS} | V _{DS} = 0 V, V _{GS} = ±20 V | – | – | ±100 | nA |

ON CHARACTERISTICS (Note 4)

| | | | | | | |
|--|-------------------------------------|---|-----|------|-----|-------|
| Gate Threshold Voltage | V _{GS(TH)} | V _{GS} = V _{DS} , I _D = 250 μA | 1.0 | – | 2.0 | V |
| Negative Threshold Temperature Coefficient | V _{GS(TH)} /T _J | – | – | –5.0 | – | mV/°C |
| Drain-to-Source On Resistance | R _{DS(on)} | V _{GS} = 10 V, I _D = 14 A | – | 7.0 | 8.0 | mΩ |
| | | V _{GS} = 4.5 V, I _D = 10 A | – | 8.8 | 9.8 | |
| Forward Transconductance | g _{FS} | V _{DS} = 10 V, I _D = 14 A | – | 30 | – | S |

CHARGES, CAPACITANCES AND GATE RESISTANCE

| | | | | | | |
|------------------------------|---------------------|--|---|------|---|----|
| Input Capacitance | C _{ISS} | V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 16 V | – | 2400 | – | pF |
| Output Capacitance | C _{OSS} | | – | 1000 | – | |
| Reverse Transfer Capacitance | C _{RSS} | | – | 375 | – | |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 4.5 V, V _{DS} = 16 V, I _D = 10 A | – | 23 | – | nC |
| Threshold Gate Charge | Q _{G(TH)} | | – | 2.0 | – | |
| Gate-to-Source Charge | Q _{GS} | | – | 5.0 | – | |
| Gate-to-Drain Charge | Q _{GD} | | – | 12 | – | |

SWITCHING CHARACTERISTICS, V_{GS} = V (Note 5)

| | | | | | | |
|---------------------|---------------------|---|---|------|---|----|
| Turn-On Delay Time | t _{d(ON)} | V _{GS} = 4.5 V, V _{DD} = 16 V, I _D = 10 A, R _G = 2.0 Ω | – | 18.5 | – | ns |
| Rise Time | t _r | | – | 70 | – | |
| Turn-Off Delay Time | t _{d(OFF)} | | – | 21 | – | |
| Fall Time | t _f | | – | 23 | – | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-------------------------|-----------------|---|------------------------|----|------|-----|---|
| Forward Diode Voltage | V _{SD} | V _{GS} = 0 V, I _S = 10 A | T _J = 25°C | – | 0.82 | 1.2 | V |
| | | | T _J = 125°C | – | 0.65 | – | |
| Reverse Recovery Time | t _{RR} | V _{GS} = 0 V, d _{ISD} /d _t = 100 A/μs, I _S = 14 A | – | 48 | – | ns | |
| Charge Time | T _a | | – | 23 | – | | |
| Discharge Time | T _b | | – | 25 | – | | |
| Reverse Recovery Charge | Q _{RR} | | – | 25 | – | nC | |

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

NTMS4503N

TYPICAL PERFORMANCE CURVES

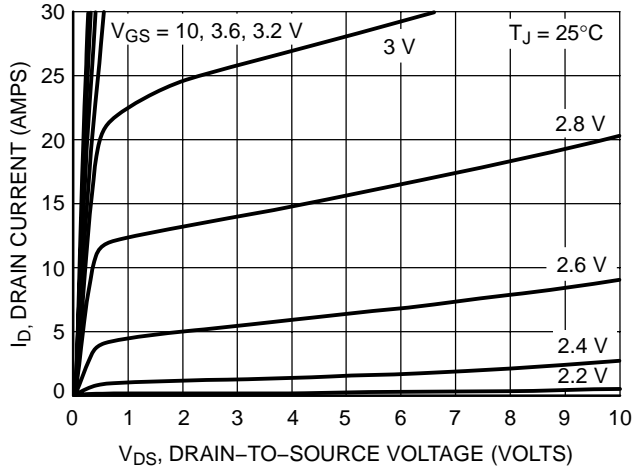


Figure 1. On-Region Characteristics

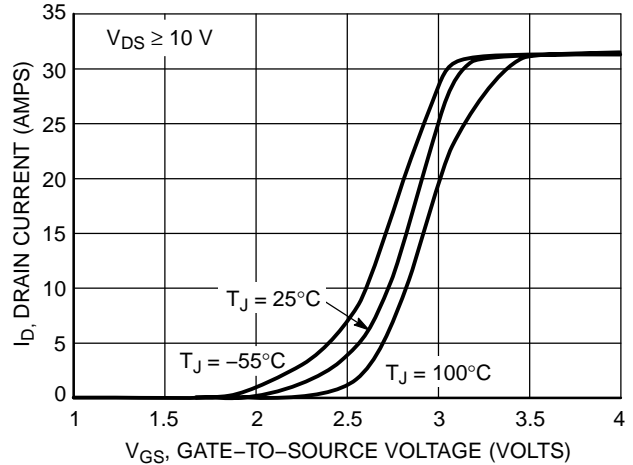


Figure 2. Transfer Characteristics

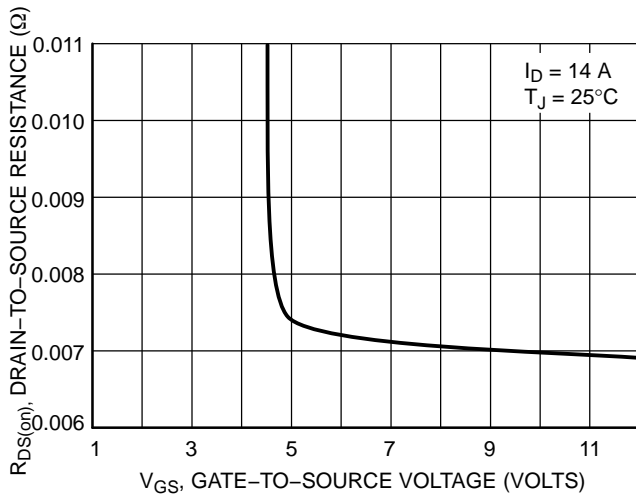


Figure 3. On-Resistance vs. Gate-to-Source Voltage

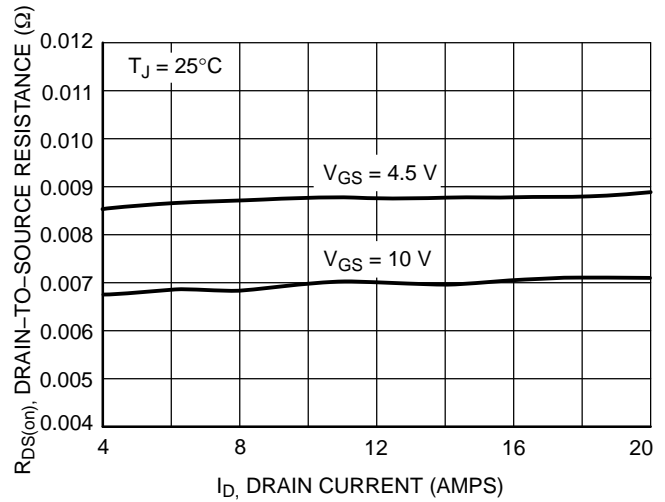


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

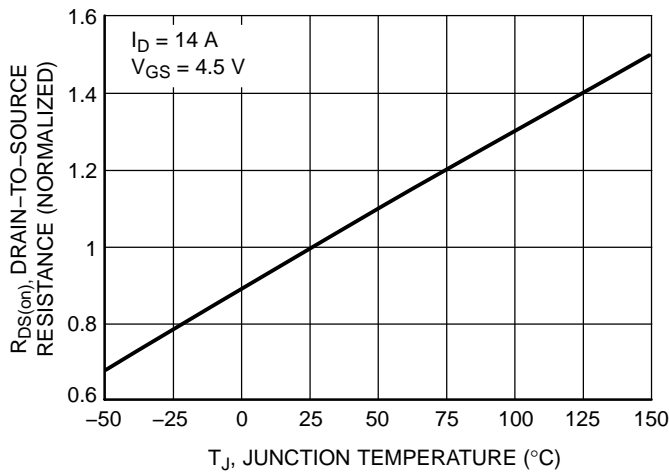


Figure 5. On-Resistance Variation with Temperature

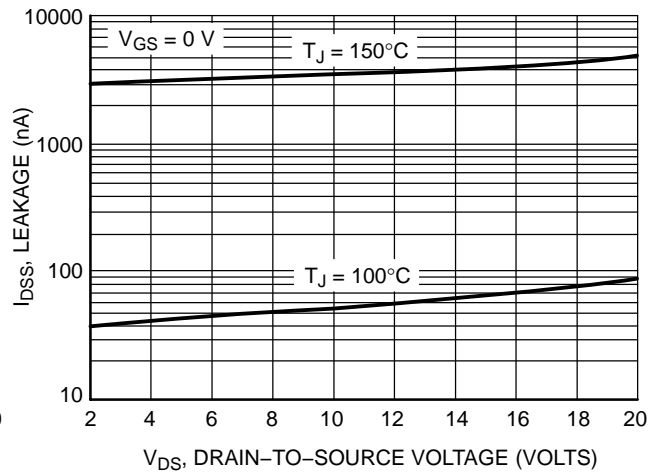


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

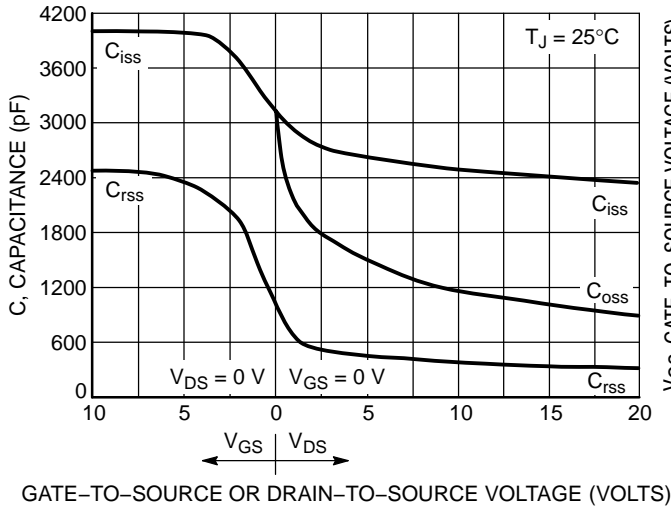


Figure 7. Capacitance Variation

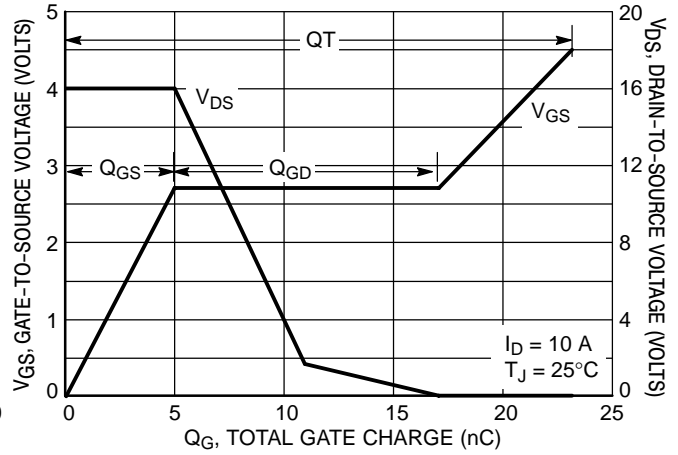


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

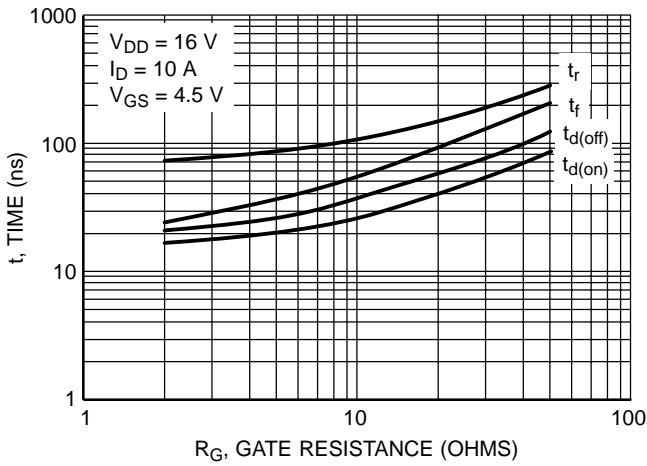


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

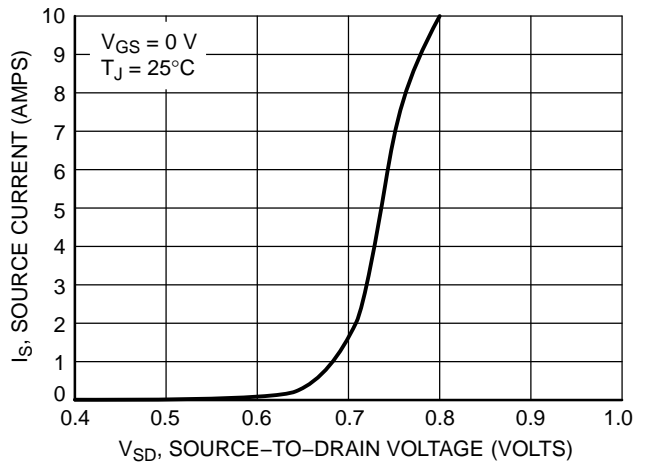


Figure 10. Diode Forward Voltage vs. Current

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC | | 0.050 BSC | |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0° | 8° | 0° | 8° |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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ISSUE AK

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- | | | | |
|--|---|---|---|
| <p>STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER</p> | <p>STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1</p> | <p>STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1</p> | <p>STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE</p> |
| <p>STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE</p> | <p>STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE</p> | <p>STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd</p> | <p>STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1</p> |
| <p>STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON</p> | <p>STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND</p> | <p>STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1</p> | <p>STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN</p> |
| <p>STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN</p> | <p>STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN</p> | <p>STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON</p> | <p>STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1</p> |
| <p>STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC</p> | <p>STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE</p> | <p>STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1</p> | <p>STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN</p> |
| <p>STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6</p> | <p>STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND</p> | <p>STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT</p> | <p>STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE</p> |
| <p>STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT</p> | <p>STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC</p> | <p>STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN</p> | <p>STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN</p> |
| <p>STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1</p> | <p>STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1</p> | | |

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